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Digital Object Identifier 10.1109/MWSYM.2002.1011607 AbstractPlus | Full Text: PDE(424 KB) IEEE CNF Rights and Permissions 6. Extracting a polynomial ac FET model with thermal couplings from S-parameter measureme Vuolevi I: Pahlonen T: Circuits and Systems, 2001, ISCAS 2001, The 2001 IEEE International Symposium on Volume 3, 6-9 May 2001 Page(s):461 - 464 vol. 2 Digital Object Identifier 10.1109/ISCAS.2001.921347 AbstractPlus | Full Text: PDF(328 KB) IEEE CNF Rights and Permissions 7. A robust high voltage Si LDMOS model extraction process to achieve first pass linear RFIC a Pla, J.A.; Bridges, D.; Radio Frequency Integrated Circuits (RFIC) Symposium, 2002 IEEE 2-4 June 2002 Page(s):347 - 350 Digital Object Identifier 10.1109/RFIC.2002.1012064 AbstractPlus | Full Text: PDE(426 KB) | IEEE CNF Rights and Permissions 8. A new physics based dynamic electro thermal large signal model for RF LDMOS FETs Versleijen, M.P.J.G.; Bloem, V.J.; van Steenwijk, J.A.; Yanson, O.I.; Microwave Symposium Digest, 2004 IEEE MTT-S International Volume 1, 6-11 June 2004 Page(s):39 - 42 Vol.1 Digital Object Identifier 10.1109/MWSYM.2004.1335792 AbstractPlus | Full Text: PDF(371 KB) IEEE CNF Rights and Permissions 9. Device modeling for III-V semiconductors - an overview Root, D.E.; Iwamoto, M.; Wood, J.; Compound Semiconductor Integrated Circuit Symposium, 2004, IEEE 24-27 Oct. 2004 Page(s):279 - 282 AbstractPlus | Full Text: PDE(642 KB) IEEE CNF Rights and Permissions 10. Simulation and measurement of thermal stress in quasi-monolithic Integration technology (Q Joodaki, M.; Kompa, G.; Leinhos, T.; Kassing, R.; Hillmer, H.; Electronic Components and Technology Conference, 2001, Proceedings, 51st 29 May-1 June 2001 Page(s):715 - 720 Digital Object Identifier 10.1109/ECTC.2001.927811 AbstractPlus | Full Text: PDF(1248 KB) IEEE CNF Rights and Permissions 11. Electro-thermal model of an optical transmitter Karray, M.; Desgreys, P.; Charlot, J.-J.; Industrial Technology, 2003 IEEE International Conference on Volume 2, 10-12 Dec. 2003 Page(s):751 - 753 Vol.2 Digital Object Identifier 10.1109/ICIT.2003.1290750 AbstractPlus | Full Text: PDF(1352 KB) IEEE CNF Rights and Permissions 12. Nonlinear transistor modelling based on measurements results Quere, R.; Teyssier, J.P.; Viaud, J.P.; Obregon, J.; Integrated Nonlinear Microwave and Millimeterwave Circuits, 1994, Third International Workshop on 5-7 Oct. 1994 Page(s):27 - 41 Digital Object Identifier 10.1109/INMMC.1994.512511 AbstractPlus | Full Text PDF(1016 KB) IEEE CNF

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 A new large-signal model based on pubs measurement techniques for RF power MOSFET Collantes, J.M., Raoux, J.J., Villotte, J.P., Quere, R., Montoriol, G., Oupis, F.; Microwere Symposium Diseas 1985. IEEE MITS. International 16-20 May 1995 Pages(s):1553 - 1556 vol. 3 Digital Object Identifier 10 1109/MNSVM 1995.406271 AbstractEyles Full Text: EDE(406 KB). IEEE CMF
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 Power GaAs FET temperature dependent modeling and circuit simulation validation Gao Xuebang, Guo Birghui; Microwneve and Millimeter Veives I schnology Proceedings. 1998. ICMMT '98. 1998 International Co. 18-20 Aug. 1999 Page(s):116-119 Digital Object Identifier 10.1109/ICMMT.1998.768240
Abstract/bis Full Text PDE(184 KB) IEEE CNF Roths and Permissions
15. An optimized method for computer-aided DC measurements of power MOS transistors Gracia, J. Aranosta, F.J. Instrumentation and Measurement. IEEE Transistions on Volume 37, Issue 3, Sept. 1988 Page(s) 393 - 397 Dejtat Oleye identifier 10.1109/19.7422 AbstratsElus Full Text PDE(SS KB) IEEE JNL
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16. Improvements in three-terminal thermoconverter technique Bergesst, R.; Chatzopoulos, Z.; Grno, L.; Ilherfield, W.G.; Lalinisky, T.; Kluzmik, J.; Pricision Electromannétic Messariments Diasest. 1996 Conference on 17-21 June 1996 Page(s) 564 Detail Object Identifier 10.1108/CPEM. 1996.64795 Abstract@bla Full Text PEDE(76 KB) IEEE CNF
Rights and Permissions
17. Broad-band characterization of FET self-heating Parier, A.E., Rathmell, J.G.; Microwwar, Broby and Techniques, LEEE Transactions on Volume S3, Issue 7, July 2005 Page(s) 2242-2429 Olgital Object Identifier 10.1109/mTT.2005.850399 Abstrace/Lus Full Text: PDE(S04 KB) IEEE JNL Bights and Permissions

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	-	1	Multi-scale thermal analysis of GaAs RF device J. L., Coosioli, R., Nary, K.; Canfield, P.; Semiconductor. Thermal Measurement and Manasement 15-17 March 2005 page(e):529-528 Digital Object Identifier 10.1108/STHERM. 2005.1412189 abstractPlus Full Text EDE(1129 KB) IEEE CNF Boths and Permissions	Symposium, 2005 IEEE Twenty, First An

	Ibrahim, M.S., Paradis, L.R., Paterson, D.; Semionodividor Thermal Mississement and Management Symposium, 1991, SEMI-THERM VIII. Pro- Annual LEEE: 12-14 Feb. 1991 Page(s) 80 - 85 Optia Object Identifier 10 1109/STHERM 1991, 152917 Abstrace/Day, Full Text DECE(780 KB) IEEE CNF Bights and Permissions
	Finite element modelling of a MMIC transmitter module for thermal/structural design optimiza forthim, M.S.; Paradis, L.R.; Paterson, D.; Components, Hybrids, and Manufacturing Technology, JEEE Transactions on fees also JEEE TransPackagain, and Manufacturing Technology, Part A. B. C.J. Volume 15, Issue 5, Oct 1992 Page(9):723 - 729 Ogital Object Identifier 10 1109/33 180006 AbstractPlus I Full Text EDC(1164 KB) IEEE JNL Boths and Permissions
0	7. A large-signal FET model including thermal and trap effects with pulsed I-V measurements Kyoungmin Koh; Hyun-Min Park; Songcheol Hong; Microwers Symbosism Dipset, 2003 IEEE MTTS International Volume 1, 8-13 Jule 2003 Pages) 467 - 470 vol. 1 AbstraciPlus I Full Text: PDE(360 KB) IEEE CNF Bights and Permissions
	A symmetric and thermally de-embedded nonlinear FET model for wireless and microwave a Wood, J.; Rox D.E.: Microwere Symposium, Dioest, 2004 IEEE MTT-S international Volume 1, 6-11 June 2004 Page(a):35 - 38 Vol.1 Digital Cipiert Identifier 10 1103/MVSTW, 2004, 1335791 AbstractRise, Full Text: PDEC(89 KB) IEEE CNF Rothts and Permissions
	Dynamical model for GaAs optical FETs in 0-120°C temperature range Ramovc, R.; Andrin, R.; Gidovic, D.; Microelectronics, 1997. Prosedings., 1997. 21st. International Conference.on Volume 2, 14-17 Sept. 1997 Page(s),493 - 498 vol. 2 Optiat Opect Identifier 10.1 1090/CMEL. 1997.633876 Abstract/Exp. Full Text: PDE(292 KB) IEEE CNF Bights and Permissions
	10. Device modeling for III-V semiconductors - an overview Root, D.E., Iwamoto, M., Whood, J.; Commound Semiconductor Infegrated Circuit Symposium2004. JEEE 24-27 C2. 2004 Page(b):279 - 282 AbstradPlus Fwi Text: PDE(642 KB) IEEE CNF Broths and Permissions
	Electrothermal model of GaAs FET devices for fast PC implementation Pesane, M.; Giorgio, A.; Pern, A.G.; Circuits, Devices and Systems, IEE Proceedings See also IEE Proceedings G. Circuits, Devices an Volume 184, Sissen 1, Feb 2001 Page(6):40 - 44 Digital Object biorafiler 10.1049(ip-cds 20010173 AbstractPlus I Full Text EDE(628 KB) IEE JNL
	 Thermal analysis for improved packaging of 4-channel 42 VH4 V DC/DC converter Les, SY.; Pfleetzer, A.G.; van Wyk, J.D.; Industry Applications Conference, 2004, 38th JAS Annual Meeting, Conference Record of the 2004 Volume 4, 3-7 Oct, 2004 Page(s) 2330 - 2330 vc4 4 Draito Chiefe Interfersity 61 (101048) 2004 (19880)

AbstractPlus | Full Text; PDF(643 KB) | IEEE CNF Rights and Permissions 13. A new physics based dynamic electro thermal large signal model for RF LDMOS FETs П Versleilen, M.P.J.G.: Bloem, V.J.: van Steenwijk, J.A.; Yanson, O.I.; Microwave Symposium Digest, 2004 IEEE MTT-S International Volume 1, 6-11 June 2004 Page(s):39 - 42 Vol.1 Digital Object Identifier 10.1109/MWSYM.2004.1335792 AbstractPlus | Full Text: PDF(371 KB) | IEEE CNF Rights and Permissions 14. Thermal aspects of GaAs power FET attachment using isotropically conductive adhesive Mayer, M.; Nicolics, J.; Hanreich, G.; Mundlein, M.; Polymers and Adhesives in Microelectronics and Photonics, 2002, POLYTRONIC 2002, 2nd Interna Conference on 23-26 June 2002 Page(s):38 - 43 Digital Object Identifier 10.1109/POLYTR.2002.1020180 AbstractPlus | Full Text: PDF(755 KB) | IEEE CNF Rights and Permissions 15. A robust high voltage Si LDMOS model extraction process to achieve first pass linear RFIC a П success Pla, J.A.; Bridges, D.; Microwave Symposium Digest, 2002 IEEE MTT-S International Volume 1, 2-7 June 2002 Page(s):263 - 266 Digital Object Identifier 10.1109/MWSYM.2002.1011607 AbstractPlus | Full Text: PDF(424 KB) IEEE CNF Rights and Permissions 16. Empirical modeling of low-frequency dispersive effects due to traps and thermal phenomena Filicori, F.; Vannini, G.; Santarelli, A.; Sanchez, A.M.; Tazon, A.; Newport, Y.; Microwave Theory and Techniques. IEEE Transactions on Volume 43. Issue 12, Part 2, Dec. 1995 Page(s):2972 - 2981 Digital Object Identifier 10,1109/22.475663 AbstractPlus | Full Text: PDE(1000 KB) IEEE JNL Rights and Permissions 17. Analytical approach to evaluate thermal reduction effects of peripheral structures on microw device chips Yanagawa, S.; Microwave and Wireless Components Letters, IEEE [see also IEEE Microwave and Guided Wave L Volume 15, Issue 5, May 2005 Page(s):324 - 326 Digital Object Identifier 10.1109/LMWC.2005.847693 AbstractPlus | References | Full Text: PDF(176 KB) IEEE JNL Rights and Permissions 18. Extracting a polynomial ac FET model with thermal couplings from S-parameter measurement П Vuolevi, J.; Rahkonen, T.; Circuits and Systems, 2001, ISCAS 2001, The 2001 IEEE International Symposium on Volume 3, 6-9 May 2001 Page(s):461 - 464 vol. 2 Digital Object Identifier 10.1109/ISCAS.2001.921347 AbstractPlus | Full Text: PDF(328 KB) IEEE CNF Rights and Permissions 19. A robust high voltage Si LDMOS model extraction process to achieve first pass linear RFIC a SUCCESS Pla .I.A : Bridnes D : Radio Frequency Integrated Circuits (REIC) Symposium, 2002 IEEE 2-4 June 2002 Page(s):347 - 350

Digital Object Identifier 10.1109/RFIC 2002.1012064 AbstractPlus | Full Text: PDF(426 KB) IEEE CNF Rights and Permissions 20. A functional GaAs FET noise model Electron Devices, IEEE Transactions on Volume 28, Issue 5, May 1981 Page(s):511 - 517 AbstractPlus | Full Text: PDE(704 KB) | IEEE JNL Rights and Permissions 21. Nonlinear-dispersive GaAs FET drain-current model for harmonic balance simulation Eccleston, K.W.; Microwave Conference Proceedings, 1997, APMC '97., 1997 Asia-Pacific 2-5 Dec. 1997 Page(s):717 - 720 vol.2 Digital Object Identifier 10.1109/APMC.1997.654642 AbstractPlus | Full Text: PDF(284 KB) IEEE CNF Rights and Permissions 22. A new extraction method for the two-parameter FET temperature noise model Garcia, M.; Stenarson, J.; Yhland, K.; Zirath, H.; Angelov, I.; Microwave Theory and Techniques. IEEE Transactions on Volume 46, Issue 11, Part 1, Nov. 1998 Page(s):1679 - 1685 Digital Object Identifier 10.1109/22.734558 AbstractPlus | References | Full Text: PDF(280 KB) | IEEE JNL Rights and Permissions 23. Simulation and measurement of thermal stress in quasi-monolithic integration technology (Q Joodaki, M.; Kompa, G.; Leinhos, T.; Kassing, R.; Hillmer, H.; Electronic Components and Technology Conference, 2001, Proceedings, 51st 29 May-1 June 2001 Page(s):715 - 720 Digital Object Identifier 10.1109/ECTC.2001.927811 AbstractPlus | Full Text PDF(1248 KB) IEEE CNF Rights and Permissions 24. Temperature distribution In power GaAs field effect transistors using spatially resolved phot mapping Landesman, J.P.; Martin, E.; Braun, P.; Physical and Failure Analysis of Integrated Circuits, 1999. Proceedings of the 1999 7th International 5-9 July 1999 Page(s):185 - 190 Digital Object Identifier 10.1109/IPFA.1999.791331 AbstractPlus | Full Text: PDF(484 KB) IEEE CNF Rights and Permissions 25. Measurement based nonlinear electrothermal modeling of GaAs FET with dynamical trappin Ouarch, Z.; Collantes, J.M.; Teyssier, J.P.; Quere, R.; Microwave Symposium Digest, 1998 IEEE MTT-S International Volume 2, 7-12 June 1998 Page(s):599 - 602 vol.2 Digital Object Identifier 10.1109/MWSYM.1998.705064 AbstractPlus | Full Text: PDF(336 KB) IEEE CNF Rights and Permissions



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Rights and Permissions 6. Empirical modeling of low-frequency dispersive effects due to traps and thermal phenome Filicori, F.; Vannini, G.; Santarelli, A.; Sanchez, A.M.; Tazon, A.; Newport, Y.; Microwave Theory and Techniques, IEEE Transactions on Volume 43, Issue 12, Part 2, Dec. 1995 Page(s):2972 - 2981 Digital Object Identifier 10.1109/22.475663 AbstractPlus | Full Text: PDF(1000 KB) IEEE JNL Rights and Permissions 7. A new empirical model for GaAs FET in nonlinear circuit simulation Cao, J.; Lin, F.; Kooi, P.S.; Leong, M.S.; Microwave Conference Proceedings, 1997. APMC '97., 1997 Asia-Pacific 2-5 Dec. 1997 Page(s):517 - 520 vol.2 Digital Object Identifier 10.1109/APMC.1997.654592 AbstractPlus | Full Text; PDF(300 KB) IEEE CNF Rights and Permissions 8. Construct GaAs FET DC model from drain-port DC power and conductance Liu. L.: Lin. F.: Kooi. P.S.: Leong. M.S.: Microwave Conference, 1999 Asia Pacific Volume 1, 30 Nov.-3 Dec. 1999 Page(s):56 - 59 vol.1 Digital Object Identifier 10.1109/APMC.1999.828047 AbstractPlus | Full Text: PDF(136 KB) IEEE CNF Rights and Permissions 9. A table lookup FET model for accurate analog circuit simulation Rofougaran, A.; Abidi, A.A.; Computer-Aided Design of Integrated Circuits and Systems, IEEE Transactions on Volume 12 Issue 2 Feb. 1993 Page(s):324 - 335 Digital Object Identifier 10.1109/43.205011 AbstractPlus I Full Text: PDF(960 KB) IEEE JNL Rights and Permissions 10. A 110 GHz scalable FET model based on 50 GHz S-parameter measurements П Cidronali, A.: Collodi, G.: Santarelli, A.: Vannini, G.; Microwave Symposium Digest., 2000 IEEE MTT-S International Volume 3, 11-16 June 2000 Page(s):1377 - 1380 vol.3 Digital Object Identifier 10.1109/MWSYM.2000.861797 AbstractPlus | Full Text: PDF(348 KB) IEEE CNF Rights and Permissions 11. On wafer intermodulation distortion measurements on resistive FET mixers for device comp П validation Hutabarat, M.T.; Webster, D.R.; Haigh, D.G.; Schreurs, D.; van der Zanden, K.; Edgar, D.L.; Borsos Thayne, I.G.; Parker, A.E.; High Performance Electron Devices for Microwave and Optoelectronic Applications, 1999, EDMO, 1 22-23 Nov. 1999 Page(s);170 - 175 Digital Object Identifier 10.1109/EDMO.1999.821480 AbstractPlus | Full Text: PDF(432 KB) IEEE CNF Rights and Permissions 12. A new empirical large signal model for silicon RF LDMOS FETs Miller, M.; Dinh, T.; Shumate, E.; Whreless Applications Digest, 1997., IEEE MTT-S Symposium on Technologies for 23-26 Feb. 1997 Page(s):19 - 22 Digital Object Identifier 10.1109/MTTTWA.1997.595103

AbstractPlus | Full Text: PDF(337 KB) IEEE CNF

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	13. An accurate dc model of 2-DEG FET for implementation on a circuit simulator Hida, H.; Inb., T.; Chata, K.; Electron Device Letters. [EEE Volume 7. Sause 6, Jun 1980 Page(e):339 - 395 AbstractPus Full Text: PDE(296 KB) IEEE JNL Routs and Permissions
	14. Millimeter-wave FET modeling using on-wafer measurements and EM simulation Octronal, A.; Collod, G.; Sartarettil, A.; Vannini, G.; Manes, G.; Microweve: Theory and I schmiques. LIEEE Iransactions on Volume 50, Issue 2. Feb. 2002 Page(s):425 - 432 Digital Object Identifier 10.1109/22.982219 Abstract/Sus Bettercases Full Text PDE(218 KB) IEEE JNL Roths and Permissions
	15. An Improved large-signal model for variactor and GaAs FET diodes Gas Xuebang, Liang Yaping, Liao Bin; Microwave Conference Proceedings, 1997. APMC 197. 1997. Asia-Pacific 2-5 Dec. 1997 Page(s) 729-732 Vol.2 Digital Object identifier 10 1109APMC 1997 654645 Abstract/Lia Full Text EDE(184 KB) IEEE CNF Bights and Permissions
	16. An improved FET model for computer simulators Parter, A.E.; Skellern, D.J.; Computer_Asked_Design of Improprietd Circulas and Systems. IEEE Transactions on Volume 9. Issue 5, May 1990 Page(s) 551 - 563 Digital Object Identifier 10.1108/43.55175 Abstract@blus Full Text PDE(192 KB) IEEE_UNL Bights and Permissions
	17. A new approach to FET model scaling and MMIC design based on electromagnetic analysis Cidronal, A.; Collodi, G.; Varnini, G.; Santarelli, A.; Microwene, Pheno; and Techniuse, JEEE Transactions on Volume 47, Issue 6, Pert 2, June 1959 Page(e):900 - 907 Optial Object Identifier 10, 1109/22, 769324 Abstract/Bus, Beferences Full Text EDE(252 KB) IEEE JNL Bights and Permissions
D	18. Semi-empirical SPICE models for carbon nanotube FET logic Dwyer, C.; Cheung, M.; Sonin, D.J.; Nanotechnologo, 2004. 4th IEEE Conference.on 16-19 Aug. 2004 Page(e): 386 - 388 6 logistal Object Identifier 10.1109/NANO. 2004.1392359 AbstractPlus Full Text: PDE(558 KB) IEEE CNF Bights and Permissions
	19, Modeling the drain current of the dual-gate GBAS MESFET brahim, M., Syrett, B.; Bennett, J.; Microwave Symposium Dipiest, 2003. IEEE MIT-S. International Volume 3, 8-13 June 2003 Page(s):2113 - 2116 vol.3 Abstracti
	A balanced Ka-Band GaAs FET MMIK frequency doubler Abdo-Tuko, M.; Bertenburg, R.; Wolff, L.;

Microwave and Guided Wave Letters IEEE [see also IEEE Microwave and Wireless Components I. Volume 4, Issue 7, July 1994 Page(s):217 - 219 Digital Object Identifier 10.1109/75.298245 AbstractPlus | Full Text: PDF(236 KB) IEEE JNL Rights and Permissions 21. Analytical analysis of noise figures in FET resistive mixers Won Ko; Youngwoo Kwon; Electronics Letters Volume 35, Issue 14, 8 Jul 1999 Page(s):1169 - 1170 Digital Object Identifier 10.1049/el:19990791 AbstractPlus | Full Text: PDE(216 KB) IEE JNL 22. A two-dimensional numerical FET model for DC, AC, and large-signal analysis Reiser, M.; Electron Devices, IEEE Transactions on Volume 20. Issue 1. Jan 1973 Page(s):35 - 45 AbstractPlus | Full Text: PDF(1192 KB) IEEE JNL Rights and Permissions 23. Hot-carrier effects in MOSFET's with nitrided-oxide gate-dielectrics prepared by rapid therma Hori, T.; Yasui, T.; Akamatsu, S.; Electron Devices, IEEE Transactions on Volume 39. Issue 1. Jan. 1992 Page(s):134 - 147 Digital Object Identifier 10.1109/16.108222 AbstractPlus | Full Text: PDF(1272 KB) | IEEE JNL Rights and Permissions 24. Low-Noise Low-Distortion GaAs FET Amplifiers for 6 GHz Single Sideband Radio Agarwal, K.K.; Kuo, Y.L.; Microwave Symposium Digest, MTT-S International Volume 78, Issue 1, Jun 1978 Page(s):393 - 395 AbstractPlus | Full Text PDF(176 KB) | IEEE CNF Rights and Permissions 25. Investigation of the physical mechanisms governing the performance of OEIC-compatible plateral injection lasers Sargent, E.H.; Xu, J.M.; Lasers and Electro-Optics Society Annual Meeting, 1996, LEOS 96, IEEE Volume 1, 18-19 Nov. 1996 Page(s):314 - 315 vol.1 Digital Object Identifier 10.1109/LEOS.1996.565258 AbstractPlus | Full Text: PDF(168 KB) IEEE CNF

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			2.	Jianjun Xu; Yagou Microwave Theon Volume 51, Issue Digital Object Idea	ub, M.C.E.; Run y and Technique e 1, Part 1, Jan ntifier 10.1109/1	sis for neural-based tao Ding; Qi Jun Zh es, JEEE Transactio n. 2003 Page(s):226 FMTT. 2002 806910 Fext: PDF(661 KB)	ang; ns.on - 237	ve modeling and des	sign
			3.	Microwave Theory Volume 47, Issue Digital Object Idea	nle-based FET r man, N.; Stenars y and Technique e 12, Dec. 1999 ntifier 10.1109/2 ferences Full 1	son, J.; Garcia, M.; Z es. IEEE Transactio Page(s):2350 - 235	ns.on 57		
			4.	Microwave Sympo Volume 2, 13-19 Digital Object Iden	man, N.; Stenars osium Digest. 1! June 1999 Pag ntifier 10.1109/N Il Text: <u>PDF</u> (332	model son, J.; Garcia, M.; 2 999 EEE MTT-S Inf e(s):525 - 528 vol.2 WWSYM. 1999.7798: 2 KB) IEEE CNF	emational		
			5.	Davis, B.; White, Microwave Sympo	C.; Reece, M.A. osium Digest. 2	MT model using ne ;; Bayne, M.E., Jr.; 1 003 IEEE MTT-S Int (s):177 - 180 vol.1	'hompson,	rks for CAD W.L., II; Richardson, I	N.L.; Walker, L

AbstractPlus | Full Text PDF(337 KB) IEEE CNF Rights and Permissions 6. Empirical modeling of low-frequency dispersive effects due to traps and thermal phenom Filicori, F.; Vannini, G.; Santarelli, A.; Sanchez, A.M.; Tazon, A.; Newport, Y.; Microwave Theory and Techniques, IEEE Transactions on Volume 43, Issue 12, Part 2, Dec. 1995 Page(s):2972 - 2981 Digital Object Identifier 10.1109/22.475663 AbstractPlus | Full Text: PDF(1000 KB) | IEEE JNL Rights and Permissions 7. A new empirical model for GaAs FET in nonlinear circuit simulation Cao, J.; Lin, F.; Kooi, P.S.; Leong, M.S.; Microwave Conference Proceedings, 1997, APMC '97, 1997 Asia-Pacific 2-5 Dec. 1997 Page(s):517 - 520 vol.2 Digital Object Identifier 10.1109/APMC.1997.654592 AbstractPlus | Full Text: PDF(300 KB) | IEEE CNF Rights and Permissions 8. Construct GaAs FET DC model from drain-port DC power and conductance Liu. L.; Lin. F.; Kooi, P.S.; Leong, M.S.; Microwave Conference, 1999 Asia Pacific Volume 1, 30 Nov.-3 Dec. 1999 Page(s):56 - 59 vol.1 Digital Object Identifier 10.1109/APMC.1999,828047 AbstractPlus | Full Text: PDF(136 KB) | IEEE CNF Rights and Permissions 9. A table lookup FET model for accurate analog circuit simulation Rofougaran, A.; Abidi, A.A.; Computer-Aided Design of Integrated Circuits and Systems, IEEE Transactions on Volume 12. Issue 2. Feb. 1993 Page(s):324 - 335 Digital Object Identifier 10.1109/43.205011 AbstractPlus | Full Text: PDF(960 KB) | IEEE JNL Rights and Permissions 10. A 110 GHz scalable FET model based on 50 GHz S-parameter measurements Cidronali, A.; Collodi, G.; Santarelli, A.; Vannini, G.; Microwave Symposium Digest, 2000 IEEE MTT-S International Volume 3, 11-16 June 2000 Page(s):1377 - 1380 vol.3 Digital Object Identifier 10.1109/MWSYM.2000.861797 AbstractPlus | Full Text: PDF(348 KB) | IEEE CNF Rights and Permissions 11. On wafer intermodulation distortion measurements on resistive FET mixers for device comp validation Hutabarat, M.T.; Webster, D.R.; Haigh, D.G.; Schreurs, D.; van der Zanden, K.; Edgar, D.L.; Borsos Thayne, I.G.; Parker, A.E.; High Performance Electron Devices for Microwave and Optoelectronic Applications, 1999, EDMO, 1 22-23 Nov. 1999 Page(s):170 - 175 Digital Object Identifier 10.1109/EDMO.1999.821480 AbstractPlus | Full Text: PDF(432 KB) IEEE CNF Rights and Permissions 12. A new empirical targe signal model for silicon RF LDMOS FETs Miller, M.; Dinh, T.; Shumate, E.; Wireless Applications Digest, 1997. IEEE MTT-S Symposium on Technologies for 23-26 Feb. 1997 Page(s):19 - 22 Digital Object Identifier 10.1109/MTTTWA 1997.595103 AbstractPlus | Full Text: PDF(328 KB) IEEE CNF

13. An accurate dc model of 2-DEG FET for implementation on a circuit simulator Hida, H; Ibb, T; Chetat, K; Electron Device Letters. LEEE Volume 7. Issue 6, Jun 1986 Page(s):333 - 395 AbstractPus Full Text PDE(296 KB) IEEE JNL Rights and Permissions
14. Millimeter-wave FET modeling using on-wafer measurements and EM simulation Cidronal, A.; Colod, G.; Sardarelli, A.; Vannini, G.; Manes, G.; Microwen: Propsy and Techniques, IEEE Ernanschlons on Votume 50, Issue 2, Feb. 2002 Page(s) 425 - 432 Optiad Object Identifier 10.1109/22.902219 AbstractDess InSertences, IFull Text: PDE(218 KB) IEEE JNL. Bights and Permissions
15. An improved large-signal model for varactor and GuAs FET diodes Gso Xuebang, Liany Yaping, Liao Bin, Microwave Conference Proceedings, 1987. APIAC '97., 1997. Asia-Pacific 2-5 Dec. 1997 Page(s):729 - 732 vol.2 Dipital Object Identifier 10. 1109/APIAC. 1997. 654645 AbstractPlus i Full Text: PDE(184 KB) IEEE CNF Bioths and Parmissions
 An improved FET model for computer simulators Parker, A.E.; Skellem, D.J.; Computer.Alkeld. Design of Indigrated. Circuits and Systems. JEEE Transactions on Volume 9, Sun 5, May 1990 Page(s):551 - 563 Digital Object Identifier 10.1108/43.55175 AbstractPlus Full Text: PDE(192 KB) IEEE JNL Rights and Permissions
17. A new approach to FET model scaling and MMIC design based on electromagnetic analysis Cidronali, A.; Coltodi, G.; Vannini, G.; Santaretil, A.; Microwave, Theory and Techniques, LEEE Transactions on Volume 47, Susse C, Part 2, user 1999 Page(s) 900 - 907 Digital Object Identifier 10.1109/22.769324 AbstractPlas References Full Text: PDE(252 KB) IEEE JNL Rights and Permissions
18. Semi-empirical SPICE models for carbon nanotable FET logic Dwyer, C.; Cheung, M.; Sorin, D.J.; Nanotechnology. 2004. 4th. IEEE Conference on 1s-19 Aug. 2004 Page(s): 338-388 Digital Object Identifier 10.1109/NANO. 2004.1392359 Abstract2/bis I Full Text: PDE[558 KB) IEEE CNF Bights and Permissions
19. Modeling the drain current of the dual-gate GAS MESFET brainin, M.; Syrett, B.; Bennett, J.; Microware Symposium Disest. 2003 IEEE MIT-S International Microware Symposium Disest. 2003 IEEE MIT-S International Microw
Volume 3, 8-13 June 2003 Page(s)/2113 - 2116 vol 3 Abstrad2Pling Full Text: PDE(299 KB) IEEE CMF Rights and Permissions

Microwave and Guided Wave Letters. IEEE [see also IEEE Microwave and Wireless Components L Volume 4, Issue 7, July 1994 Page(s) 217 - 219 Digital Object Identifier 10, 1109/75 298245
AbstractPlus Full Text: PDE(236 KB) IEEE JNL Rights and Permissions
21. Analytical analysis of noise figures in FET resistive mixers Wen No; Youngwoo (won; Electronical Letters Volume 35, Issue 14, 8 Jul 1999 Page(s):1169 - 1170 Oglatal Object Identifier 10.1048/el:1999/791 AbstractPlus Full Text: PDE(216 KB) IEE JNL
22. A two-dimensional numerical FET model for DC, AC, and large-4-signal analysis Relser. M.; Relser. M.; Electron Devices, IEEE Transactions on Volume 20, Issue 1, Jan 1973 Page(s) 35 - 45 Abstract/Dls, I Full Text PDE(1192 KB) IEEE JNL Rights and Permissions
23. Not-carrier effects in MOSFET's with nitrided-oxide gate-dielectrics prepared by rapid therma Hon T.; Yasui, T.; Alamatsu, S.; Beston Devices, IEEE Transissictions on Volume 39, Issue 1, Jan. 1992 Page(s) 134 - 147 Deptal Devel identifier 10 1109(f) 103222 Abstract/bis Full Text PDE(1272 KB) IEEE JNL Blobts and Permissions
24. Low-Noise Low-Distortion GaAs FET Ampliffers for 6 GHz Single Sideband Radio Agarwal, K.K.; Kuo, Y.L.; Microweve Simposium Dises, MTLS International Volume 78, Issue 1, Jun 1978 Page(6):393 - 365 Abstrat2hus Full Text: PDE(176 KB) IEEE CNF Boths and Permissions
25. Investigation of the physical mechanisms governing the performance of OEIC-compatible p- tereal Injection lasers Sargert, E.H.; Xu, J.M.; Lasers and Electro-Colonia Society Annual Meeting, 1.986, LEOS 96, LEEE Volume 1, 18-19 Nov. 1996 Page(4), 314 - 315 vol.1 Opinto Object Sentine 10, 11091-EOS, 1996 550258 AbstratChis, F.Int Text EDE(169 K8) LEEE CNF Robbis and Permissions

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	Small signal 8-parameter estimation of BJTs using artificial neural networks Majd, I.; Nadeem, A.E.; e Azam, F.; Mattitook Conference. 2004. Proceedings of INMIC 2004. 8th International 24-26 Dec. 2004 Page(e): 596 973 Digital Chiject Identifier 10.1109/NNIIC.2004.195972
	AbstractPlus Full Text: PDF(246 KB) IEEE CNF Bights and Permissions
	A parameter extraction method using cutoff measurement for a large-scale HSPICE model of Seconpheam Lee, Sang Wong Karg; Bedron Devices, IEEE Transactions on Volume 41, Issue 1, Jan. 1994 Page(a):112 - 114 Dejat Objekt Identifier 10.1103/16.259629
	AbstractPus Full Text: PDE(224 KB) IEEE JNL Rights and Permissions
	 Direct measurement of C_{be} and C_{be} versus voltage for small HBTs with microwave s-parame Gummel-Poon BJT models Chang, C., Asbook, P.; Zampardi, P.; Wang, K.C.; Microwave. Theory and Techniques. IEEE Transactions on Volume 47, Issue 1, Jan. 1999 Pagi(s):108 - 110 Digital Object identifier to 11012672 740592
	AbstractPlus References Full Text PDE(120 KB) IEEE JNL Rights and Permissions
	 Sälicon BJT modeling using VBIC model Huang, G.W.; Chen, K.M.; Kuan, J.F.; Deng, Y.M.; Wen, S.Y.; Chiu, D.Y.; Wang, M.T.; Microwase Conference, 2001. APRic 2001. 2001 Asia-Basilis Vulum 1, 3 - 5 Dec. 2001 Page (3):240 - 243 vol. 1 Digital Object Identifier 10.1109/APMC 2001. 896631
	AbstractPlus Full Text: PDF(269 KB) IEEE CNF Bights and Permissions
	Optimum microwave oscillator design using small-signal S-parameters Moselhy, A. M., Found, M.; Badio Stience Conference. 1996. NRSC 96. Thirteenth National 19-21 March 1996 Panel 1957 - 525

Digital Object Identifier 10.1109/NRSC.1996.551141

AbstractPlus | Full Text: PDF(372 KB) IEEE CNF Rights and Permissions 6. Design of a broadband microwave BJT active inductor circuit Campbell, C.F.; Weber, R.J.; Circuits and Systems, 1991. Proceedings of the 34th Midwest Symposium on 14-17 May 1991 Page(s):407 - 409 vol.1 Digital Object Identifier 10.1109/MWSCAS.1991.252183 AbstractPlus | Full Text: PDF(136 KB) IEEE CNF Rights and Permissions 7. Compression analysis of a high power BJT amplifier Bandler, J.W.; Biernacki, R.M.; Cai, Q.; Chen, S.H.; Integrated Nonlinear Microwave and Millimeterwave Circuits, 1994, Third International Workshop on 5-7 Oct. 1994 Page(s):173 - 178 Digital Object Identifier 10.1109/INMMC.1994.512525 AbstractPlus | Full Text: PDF(308 KB) | IEEE CNF Rights and Permissions 8. Unconditional Stability of a Three-Port Network Characterized with S-Parameters Boehm, J.F.; Albright, W.G.; Microwave Theory and Techniques, IEEE Transactions on Volume 35, Issue 6, Jun 1987 Page(s):582 - 586 AbstractPlus | Full Text: PDF(568 KB) IEEE JNL Rights and Permissions 9. S-parameter measurement prediction for bipolar transistors using a physical device simulato Yuan, J.-S.; Eisenstadt, W.R.; Electron Devices, IEEE Transactions on Volume 35. Issue 10. Part 1. Oct. 1988 Page(s):1633 - 1639 Digital Object Identifier 10.1109/16.7365 AbstractPlus | Full Text: PDF(476 KB) | IEEE JNL Rights and Permissions 10. Improved closed-form expressions for S-parameters of BJTs using modified Gummel-Poon m Nadeem, A.E.; Eisenstadt, W.R.; Multi Topic Conference, 2003, INMIC 2003, 7th International 8-9 Dec. 2003 Page(s):202 - 207 Digital Object Identifier 10.1109/INMIC.2003.1416697 AbstractPlus | Full Text: PDF(607 KB) IEEE CNF Rights and Permissions 11. A simple model for distributed base impedance with AC verification using S-parameter meas Cho H : Burk D.E : Bipolar Circuits and Technology Meeting, 1990, Proceedings of the 1990 17-18 Sept. 1990 Page(s):106 - 109 Digital Object Identifier 10.1109/BIPOL.1990.171138 AbstractPlus | Full Text: PDF(324 KB) IEEE CNF Rights and Permissions 12. Small-signal and noise model extraction technique for heterojunction bipolar transistor at m frequencies Roux, J.P.; Escotte, L.; Plana, R.; Graffeuil, J.; Delage, S.L.; Blanck, H.; Microwave Theory and Techniques, IEEE Transactions on Volume 43, Issue 2, Feb. 1995 Page(s):293 - 298 Digital Object Identifier 10.1109/22.348087 AbstractPlus | Full Text: PDF(476 KB) | IEEE JNL

	Dectron Devices, LEEE Transactions on Volume 51, Issue 6, June 2004 Pagie(s) 1033 - 1096 Dotato Olgot Identifier 01 1010/PED 2004 8/9521 Abstract/Pus References Full Text: PDE(240 KB) IEEE JNL Rights and Permissions 17. Method for BJT transit time evaluation Zimmer, T.; Dulto, J.B.; Lewis, N.; Electronics Lotters Volume 34, Issue 20, 1 Oct. 1998 Page(s) 1979 - 1990 Abstract/Pus Full Text: PDE(252 KB) IEE JNL
	Becton Devices. LIEET Transactions on Votume 51, Issue 6, June 2004 Page(s) 1033 - 1036 Ogital Opera Identifier 10 1109/TED 2004 829521 Abstract/Pus Beferences Full Text PDE(240 KB) IEEE JNL Rights and Pomissions 17. Method for BJT transit time evaluation Zimmer, T.; Dutus, J.B.; Lewis, N.; Bectorinica, Litters
	Electron Devices. LIEEE Transactions on Volume 51, Issue 5, Due 2004 Page(s): 1033 - 1036 Digital Object Identifier 10: 1109/TED 2004 829521 Abstract/Pus References Full Text: PDE(240 KB) IEEE JNL
	 Characterization and modeling of InGaP HBT low-frequency oscillations Burton, R.S.; Dai, P.;
0	15. A new SPICE-type heterojunction bipolar transistor model for DC, microwave small-signal an circuit simulation. Ke Lu, Perry, P. (Brazil, T.J.; Microwave Symposium Digest, 1994. [IEEE MTT-S Informational 2.3-27 May 1944 Pagings); 1573 – 1582 vol. 3 Digital Object Identifier 10.1100/InVSVM.1994.335272 AbstractPus I. Full Text. PDE(441 KB) IEEE CNF Rotts and Permissions
	14. A novel cascade-based de-embedding method for on-water microwave characterization and measurement Ming-Hasing Cho, Guo-Wei Huang, Kun-Ming Chen, An-Sam Peng, Microwave Symposium Disest. 2004 IEEE MIT-S international Volume 2, 6-14 July 2004 People's 1737 - 1740 VO22 Digital Object Identifier 10 1103/N/NSYNI, 2004 1339212 AbbranaChba Full Test: PDE(308 KB) IEEE CMF Rights and Permissions
	13. A new large-signal Attack and a mode including service and services are services and services are services and service
	13. A new large-signal AlGaAs/GaAs HBT model including self-heating effects, with correspondi

Microwave Symposium Digest, 2002 IEEE MTT-S International Volume 3. 2-7 June 2002 Page(s):2141 - 2144 Digital Object Identifier 10.1109/MWSYM.2002.1012294 AbstractPlus | Full Text: PDF(434 KB) IEEE CNF Rights and Permissions 21. SiGe profile design tradeoffs for RF circuit applications Guofu Niu; Shiming Zhang; Cressler, J.D.; Joseph, A.J.; Fairbanks, J.S.; Larson, L.E.; Webster, C.S. Harame DI : Flectron Devices Meeting, 1999, IEDM Technical Digest, International 5-8 Dec. 1999 Page(s):573 - 576 Digital Object Identifier 10.1109/IEDM.1999.824219 AbstractPlus | Full Text: PDE(340 KB) | IEEE CNF Rights and Permissions 22. Stochastic approach to noise modelling of bipolar microwave transistors П Patti, F.; Miceli, V.; Spagnolo, B.; High Performance Electron Devices for Microwave and Optoelectronic Applications, 1999. EDMO, 1 22-23 Nov. 1999 Page(s):236 - 241 Digital Object Identifier 10.1109/EDMO.1999.821491 AbstractPlus | Full Text: PDF(312 KB) IEEE CNF Rights and Permissions 23. Small signal access paths silicon-BJT de-embedding Megherbi, S.; Crozat, P.; Raynaud, G.; Pone, J.-F.; Circuits and Systems, 1996, IEEE 39th Midwest symposium on Volume 1, 18-21 Aug. 1996 Page(s):277 - 280 vol.1 Digital Object Identifier 10.1109/MWSCAS.1996.594130 AbstractPlus | Full Text: PDE(360 KB) | IEEE CNF Rights and Permissions 24. A 2-50 GHz InAIAs/InGaAs-InP HBT distributed amplifier Kobayashi, K.W.; Cowles, J.; Tran, L.T.; Block, T.R.; Oki, A.K.; Streit, D.C.; Gallium Arsenide Integrated Circuit (GaAs IC) Symposium, 1996. Technical Digest 1996, 18th Ann 3-6 Nov. 1996 Page(s):207 - 210 Digital Object Identifier 10.1109/GAAS.1996.567870 AbstractPlus | Full Text PDE(344 KB) | IEEE CNF Rights and Permissions 25. On-wafer high-frequency measurement improvements Carbonero, J.L.; Joly, R.; Morin, G.; Cabon, B.; Microelectronic Test Structures, 1994. ICMTS 1994. Proceedings of the 1994 International Confere 22-25 March 1994 Page(s):168 - 173 Digital Object Identifier 10.1109/ICMTS.1994.303482 AbstractPlus | Full Text: PDE(400 KB) IEEE CNF Rights and Permissions

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